

Silicon PNP Power Transistors

2SA1209

DESCRIPTION

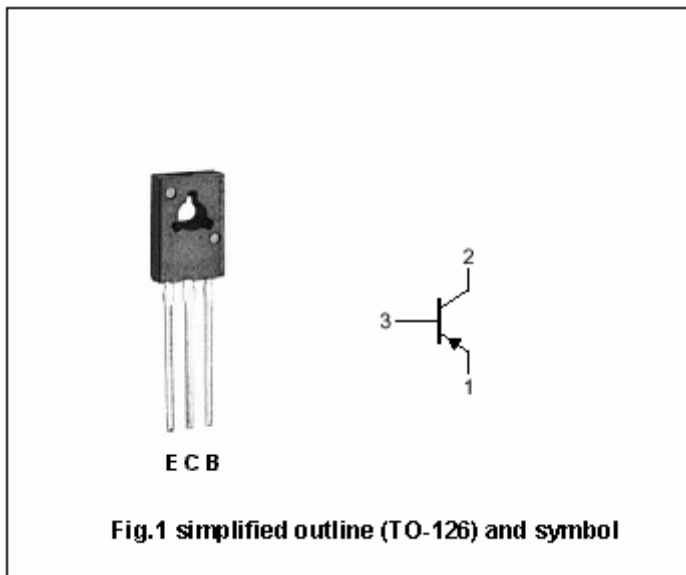
- With TO-126 package
- Complement to type 2SC2911
- High breakdown voltage
- Fast switching speed

APPLICATIONS

- High-voltage switching and AF 100W predriver applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-180	V
$V_{CEO}$	Collector-emitter voltage	Open base	-160	V
$V_{EBO}$	Emitter-base voltage	Open collector	-5	V
$I_C$	Collector current		-0.14	A
$I_{CM}$	Collector current-Peak		-0.20	A
$P_C$	Collector power dissipation	$T_a=25^{\circ}C$	1.0	W
		$T_C=25^{\circ}C$	10	
$T_j$	Junction temperature		150	$^{\circ}C$
$T_{stg}$	Storage temperature		-55~150	$^{\circ}C$

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-50mA; I <sub>B</sub> =-5mA			-0.4	V
I <sub>CB0</sub>	Collector cut-off current	V <sub>CB</sub> =-80V; I <sub>E</sub> =0			-0.1	μ A
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-4V; I <sub>C</sub> =0			-0.1	μ A
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-10mA ; V <sub>CE</sub> =-5V	100		400	
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-10mA ; V <sub>CE</sub> =-10V		150		MHz
C <sub>ob</sub>	Output capacitance	I <sub>E</sub> =0 ; V <sub>CB</sub> =-10V;f=1MHz		4.0		pF

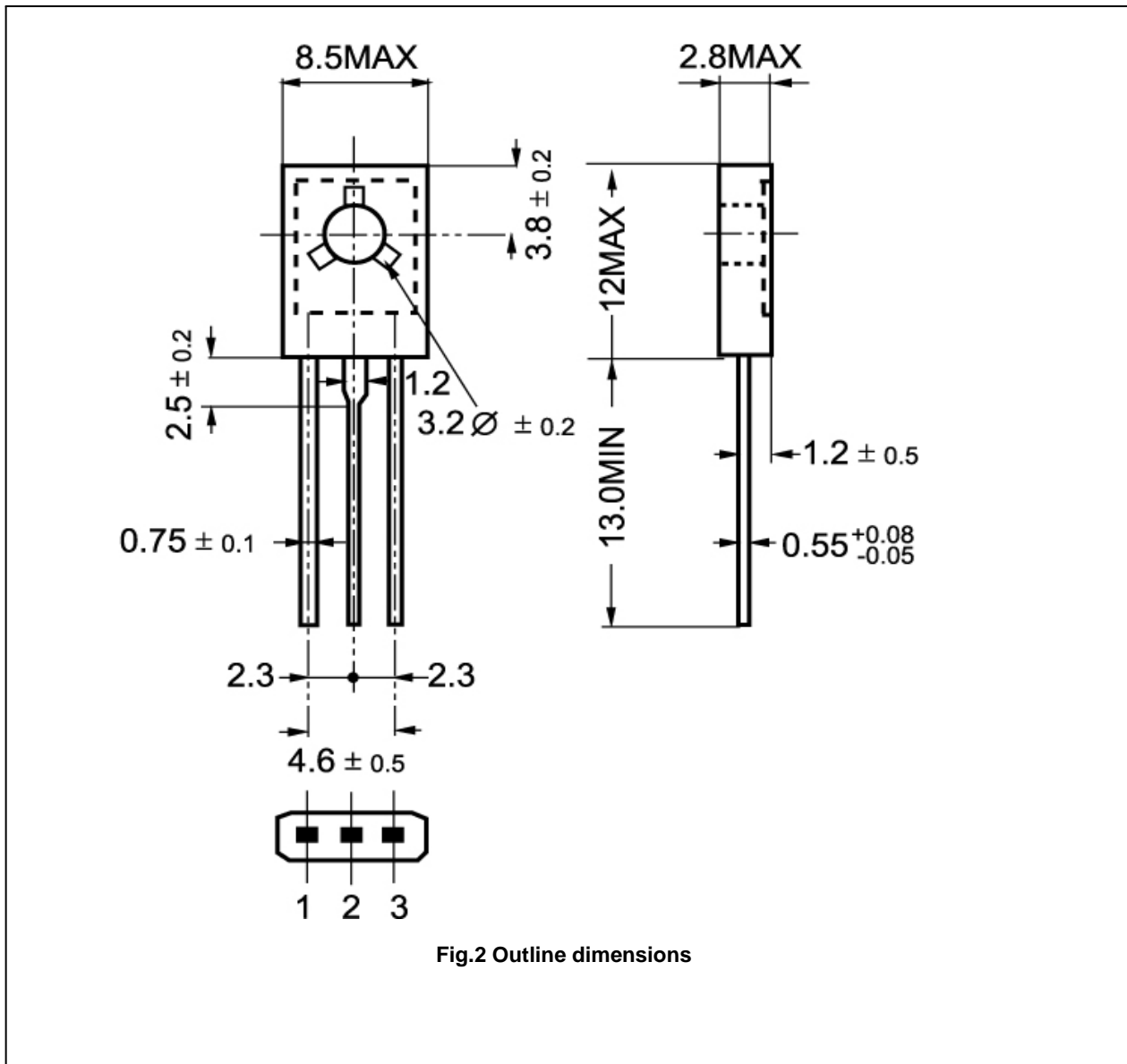
Switching times resistive load

t <sub>on</sub>	Turn-on time	I <sub>C</sub> =10mA I <sub>B1</sub> =-I <sub>B2</sub> =1mA		0.1		μ s
t <sub>s</sub>	Storage time			1.5		μ s
t <sub>f</sub>	Fall time			0.1		μ s

◆ h<sub>FE</sub> Classifications

R	S	T
100-200	140-280	200-400

PACKAGE OUTLINE



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